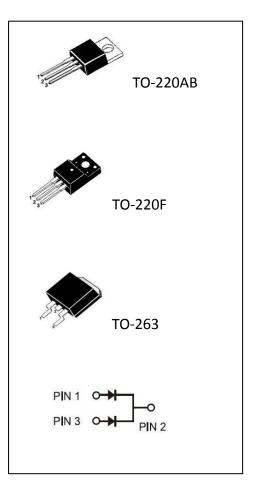


Schottky Barrier Rectifiers

Using the Schottky Barrier principle with a Refractory metal capable of high temperature operation metal. The proprietary barrier technology allows for reliable operation up to 150°C junction temperature. Typical application are in switching Mode Power Supplies such as adaptors, charger, DC/DC converters and polarity protection diodes.

Features

- Low Forward Voltage.
- Low Switching noise.
- High Current Capacity.
- Guarantee Reverse Avalanche.
- Guard-Ring for Stress Protection.
- Low Power Loss & High efficiency.
- 150°C Operating Junction Temperature.
- Low Stored Charge Majority Carrier Conduction.
- Flammability Classification 94V-O.
- Lead free in compliance with EU RoHS 2011/65/EU directive.



Maximum Ratings (Per Leg) at Ta=25°C unless otherwise specified

Characteristics	Symbol	MBR30 100	MBR30 150	MBR30 200	Unit
Maximum Repetitive Peak Reverse Voltage Working Peak Reverse Voltage Maximum DC Blocking Voltage	VRRM VRWM VR	100	150	200	V
RMS Reverse Voltage	VR(RMS)	70	105	140	V
Average Rectifier Forward Current (per diode) Total Device (Rated VR), Tc=125°C	lo		15 30		А
Peak Forward Surge Current,8.3 ms Single Half Sine-wave	İFSM	350	330	300	А
Operating and Storage Jemperature Temperature Range	TJ, Tstg	-40 to +150		°C	
Typical Thermal Resistance junction to case (per device)	Rθj-c	3.2		°C/W	

Electrical Characteristics (Per Leg) unless otherwise specified

Characteristics		Symbol		R30 00		R30 50		R30 00	Unit
Maximum Instantaneous Forward Voltage (per diode) (IF =15Amp TC = 25℃)			Туре	MAX	Туре	MAX	Туре	MAX	
		VF	0.81	0.88	0.84	0.92	0.89	0.99	V
Maximum Instantaneous Reverse Current	TA=25°C		0.6	10	1.5	10	1.5	10	μΑ
	TA=125°C	I _R	0.6	-	1	-	1.5	-	μΑ

MBR30100xT-MBR30200xT

Figure 1. Forward Current Derating Curve

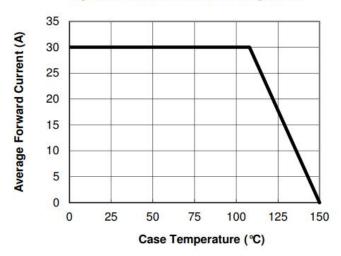


Figure 2. Maximum NON-Repetitive

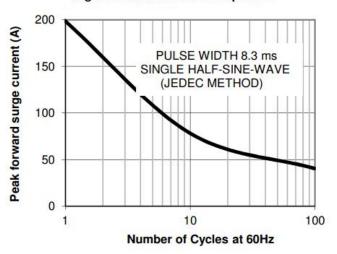


Figure 5. Typical Junction Capacitance

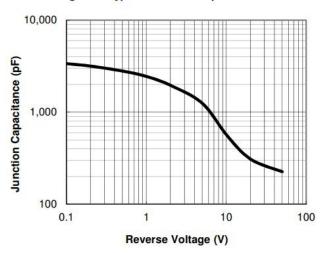


Figure 4. Typical Reverse Characteristics

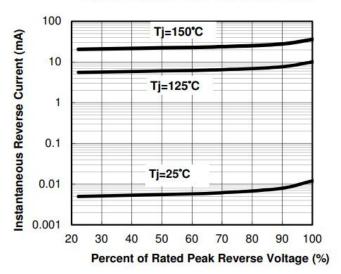


Figure 7. Typical Forward Characteristics

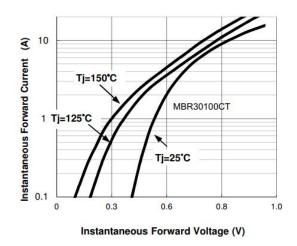
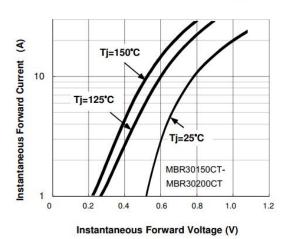
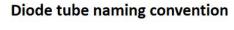


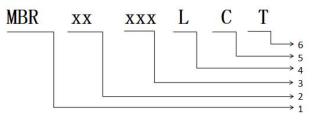
Figure 8. Typical Forward Characteristics



MBR30100xT-MBR30200xT

Marking on the body





- 1: MBR: Schottky MUR: Recovery
- 2: Mean forward current(A)
- 3: Schottky: Maximum withstand voltage (V)
 Recovery: Maximum withstand voltage *10(V)
- 4: Blank: Regular product
 L: Low Vf products
 - S: Ultra-low Vf products
- 5: Package

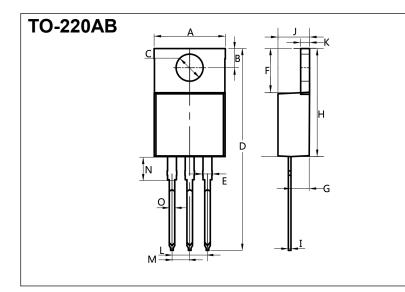
FC: TO-220F C: TO-220AB B: TO-263

D: TO-252 U: TO-251 W: TO-3P/TO-247

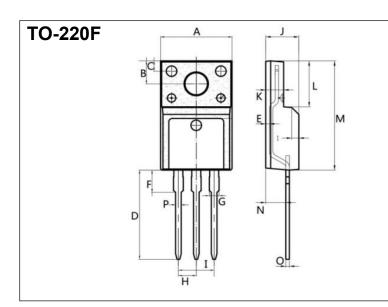
6:Series no. :

T: Regular products B: big chips

Package Outline Dimensions millimeters



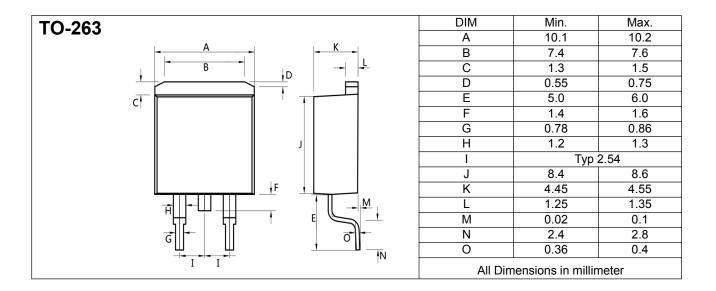
DIM	Min. Max.				
Α	10.15 10.35				
В	2.65 3.0				
С	3.7	3.9			
D	28.5 29				
E	1.3 1.45				
F	6.35	6.55			
G	2.9	3.3			
H	15.0 16.				
I	0.38	0.4			
J	4.45	4.55			
K	1.25	1.35			
L	Typ 5.08				
M	Typ 2.54				
N	3.1 3.3				
0	0.76 0.84				
All Dimensions in millimeter					



DIM	Min. Max.				
Α	9.9	10.3			
В	2.9	3.5			
С	1.15	1.45			
D	12.75	13.45			
E	0.55	0.75			
F	3.1	3.5			
G	1.25	1.45			
Н	Typ 2.54				
I	Typ 5.08				
J	4.55	4.75			
K	2.4	2.7			
L	6.35	6.75			
M	15.0	16.0			
N	2.75	3.15			
0	0.45	0.60			
Р	0.7	0.9			
All Dimensions in millimeter					



MBR30100xT-MBR30200xT



Statement:

- We reserve the right to change the manual without prior notice! Customers should obtain the latest version of the information before placing an order, and verify that the relevant information is complete and up-to-date.
- ◆ Any semiconductor product has the possibility of failure or failure under specific conditions. The buyer has the responsibility to comply with safety standards and take safety measures when using Silan product for system design and complete machine manufacturing, so as to avoid the occurrence of personal injury or property loss caused by potential failure risk!
- Product promotion will never end, our company will wholeheartedly provide customers with more excellent products!